

a complimentary acid, said complimentary acid being selected from the group consisting of phosphoric acid, hydrochloric acid, and combinations thereof;

a non-aqueous solvent, said non-aqueous solvent being selected from the group consisting of ethylene glycol, propylene carbonate, and blends thereof; and

a surface passivation agent, said passivation agent comprising ascorbic acid, wherein

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said conditioning solution is substantially free of water, and said fluorine source, said complimentary acid, said non-aqueous solvent and said passivation agent are present in said conditioning solution in concentrations suitable for the selective removal of said residues relative to any exposed metal on said semiconductor substrate.

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144. (Amended) The solution of claim 142, wherein said passivation agent contributes to said selective removal by said solution by passivating said any exposed metal on said semiconductor substrate.

146. (Amended) The solution of claim 142, wherein said fluorine source contributes to said selective removal by said solution by substantially remaining in molecular form.

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147. (Amended) The solution of claim 146, wherein said complimentary acid is present in sufficient amount to contribute to said fluorine source substantially remaining in molecular form.

148. (Amended) The solution of claim 142, wherein said fluorine source, said complimentary acid, said passivation agent, and said non-aqueous solvent are present in said solution in sufficient concentrations to suppresses the solubility of aluminum fluoride.

Sub 3 150. (Three Times Amended) A conditioning solution for use in removing residues remaining on a semiconductor substrate after a dry etch process, said conditioning solution comprising:

D4 hydrofluoric acid or ammonium fluoride;

hydrochloric acid or phosphoric acid;

ethylene glycol or propylene carbonate; and

ascorbic acid acting as a surface passivation agent.

D5 151. (Amended) The solution of claim 150, wherein said conditioning solution is substantially non-aqueous and is selective to the removal of said residues relative to exposed surfaces of metal lines over said semiconductor substrate.

152. (Amended) The solution of claim 150, wherein said passivation agent contributes to said selective removal by said solution by passivating said metal lines over said semiconductor substrate.

Sub 4
D6 154. (Amended) The solution of claim 150, wherein said hydrofluoric acid or ammonium fluoride contributes to said selective removal by said solution by substantially remaining in molecular form.

155. (Amended) The solution of claim 154, wherein said hydrochloric acid or phosphoric acid is present in sufficient amount to contribute to said hydrofluoric acid or ammonium fluoride substantially remaining in molecular form.

Sub 156 } 156. (Amended) The solution of claim 150, wherein said hydrofluoric acid or
ammonium fluoride, said hydrochloric acid or phosphoric acid, said ethylene glycol or
propylene carbonate, and said ascorbic acid are present in said solution in sufficient
concentrations to suppresses the solubility of aluminum fluoride.

Sub 158 } 158. (Three Times Amended) A conditioning solution for use in removing
residues remaining on a semiconductor substrate after a dry etch process consisting essentially
of a fluorine source, a complementary acid, a non-aqueous solvent and a surface passivation
agent, wherein

D? said conditioning solution is substantially non-aqueous and is selective to removal of
said residues relative to metal lines exposed over surfaces of said semiconductor substrate.

Please cancel claims 143, 145, 149, 153, and 157, without prejudice to their
underlying subject matter.